











CSD18532NQ5B

SLPS440C -JUNE 2013-REVISED FEBRUARY 2018

# CSD18532NQ5B 60-V N-Channel NexFET™ Power MOSFET

#### **Features**

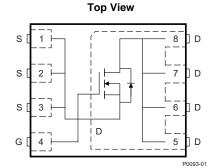
- Ultra-Low  $Q_g$  and  $Q_{gd}$
- Low-Thermal Resistance
- Avalanche Rated
- Lead-Free Terminal Plating
- **RoHS Compliant**
- Halogen Free
- SON 5-mm x 6-mm Plastic Package

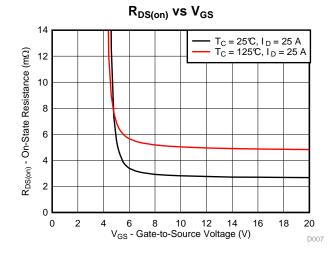
# **Applications**

- DC-DC Conversion
- Secondary Side Synchronous Rectifier
- Isolated Converter Primary Side Switch
- Motor Control

# **Description**

This 60-V, 2.7-m $\Omega$ , 5-mm × 6-mm SON NexFET<sup>TM</sup> power MOSFET has been designed to minimize losses in power conversion applications.





### **Product Summary**

$T_A = 25^\circ$	С	TYPICAL VA	UNIT		
$V_{DS}$	Drain-to-Source Voltage	60	V		
$Q_g$	Gate Charge Total (10 V)	49		nC	
$Q_{gd}$	Gate Charge Gate-to-Drain	7.9	nC		
В	Drain-to-Source On-Resistance	V <sub>GS</sub> = 6 V	3.5	mΩ	
R <sub>DS(on)</sub>	Diam-to-Source On-Resistance	V <sub>GS</sub> = 10 V	2.7	11122	
$V_{GS(th)}$	Threshold Voltage 2.8				

#### **Device Information**

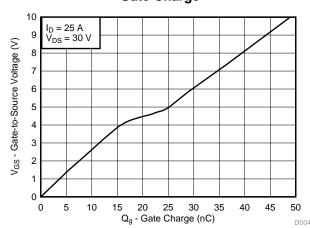
DEVICE	QTY	MEDIA	PACKAGE	SHIP
CSD18532NQ5B	2500	13-Inch Reel	SON	Tape
CSD18532NQ5BT	250	7-Inch Reel	5.00-mm × 6.00-mm Plastic Package	and Reel

#### **Absolute Maximum Ratings**

	, 10001010 1110X11110111 1 1 1 1 1 1 1 1								
$T_A = 2$	25°C	VALUE	UNIT						
$V_{DS}$	Drain-to-Source Voltage	60	V						
V <sub>GS</sub>	Gate-to-Source Voltage	±20	V						
	Continuous Drain Current (Package Limited)	100							
I <sub>D</sub>	Continuous Drain Current (Silicon Limited), $T_C = 25$ °C	151	Α						
	Continuous Drain Current <sup>(1)</sup>	21							
I <sub>DM</sub>	Pulsed Drain Current <sup>(2)</sup>	400	Α						
_	Power Dissipation <sup>(1)</sup>	3.1	14/						
$P_D$	Power Dissipation, T <sub>C</sub> = 25°C	156	W						
T <sub>J</sub> , T <sub>stg</sub>	Operating Junction Temperature, Storage Temperature	-55 to 150	°C						
E <sub>AS</sub>	Avalanche Energy, Single Pulse $I_D$ = 85 A, L = 0.1 mH, $R_G$ = 25 $\Omega$	360	mJ						

- (1) Typical  $R_{\theta JA}$  = 40°C/W on a 1-in², 2-oz Cu pad on a 0.06-in thick FR4 PCB.
- (2) Max  $R_{\theta,JC} = 0.8^{\circ}C/W$ , pulse duration  $\leq 100 \mu s$ , duty cycle  $\leq$

#### **Gate Charge**





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# **4 Revision History**

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision B (May 2017) to Revision C	Page
Extended the V <sub>DS</sub> on Figure 5 to 60 V	4
Changes from Revision A (December 2015) to Revision B	Page
Added Receiving Notification of Documentation Updates section.	7
<ul> <li>Changed the dimension between pads 3 and 4 from 0.028 inches: to 0.050 inches in the Recor Pattern section diagram.</li> </ul>	
Fattern Section diagram.	
	Page
Changes from Original (June 2014) to Revision A  Added part number to title.	1
Changes from Original (June 2014) to Revision A  Added part number to title.	1
Changes from Original (June 2014) to Revision A  Added part number to title.  Added 7" reel to Ordering Information.	1
Changes from Original (June 2014) to Revision A  Added part number to title.  Added 7" reel to Ordering Information.  Updated pulsed current conditions.	1 1 1
Changes from Original (June 2014) to Revision A  Added part number to title.  Added 7" reel to Ordering Information.  Updated pulsed current conditions.	
Changes from Original (June 2014) to Revision A  Added part number to title.  Added 7" reel to Ordering Information.  Updated pulsed current conditions.  Added line for Power Dissipation, T <sub>C</sub> = 25°C in Absolute Maximum Ratings table.	



# 5 Specifications

### 5.1 Electrical Characteristics

 $T_{\Lambda} = 25^{\circ}C$  unless otherwise stated

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
STATIC	CHARACTERISTICS				
BV <sub>DSS</sub>	Drain-to-source voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60		V
I <sub>DSS</sub>	Drain-to-source leakage current	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 48 V		1	μΑ
I <sub>GSS</sub>	Gate-to-source leakage current	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = 20 V		100	nA
V <sub>GS(th)</sub>	Gate-to-source threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.4 2.8	3.4	V
1	Designate accounts on manifestation	V <sub>GS</sub> = 6 V, I <sub>D</sub> = 25 A	3.5	4.4	0
R <sub>DS(on)</sub>	Drain-to-source on-resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 25 A	2.7	3.4	mΩ
9 <sub>fs</sub>	Transconductance	V <sub>DS</sub> = 30 V, I <sub>D</sub> = 25 A	140		S
DYNAMI	IC CHARACTERISTICS		<u>"</u>		
C <sub>iss</sub>	Input capacitance		4100	5340	pF
C <sub>oss</sub>	Output capacitance	$V_{GS} = 0 \text{ V}, V_{DS} = 30 \text{ V}, f = 1 \text{ MHz}$	495	644	pF
C <sub>rss</sub>	Reverse transfer capacitance		16	21	pF
$R_G$	Series gate resistance		1.2	2.4	Ω
Qg	Gate charge total (10 V)	V <sub>DS</sub> = 30 V, I <sub>D</sub> = 25 A	49	64	nC
$Q_{gd}$	Gate charge gate-to-drain		7.9		nC
$Q_{gs}$	Gate charge gate-to-source		16		nC
Q <sub>g(th)</sub>	Gate charge at V <sub>th</sub>		11		nC
Q <sub>oss</sub>	Output charge	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V	69		nC
t <sub>d(on)</sub>	Turnon delay time		8.2		ns
t <sub>r</sub>	Rise time	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V},$	8.7		ns
t <sub>d(off)</sub>	Turnoff delay time	$I_{DS} = 25 \text{ A}, R_G = 0 \Omega$	20		ns
t <sub>f</sub>	Fall time		2.7		ns
DIODE C	CHARACTERISTICS			·	
$V_{SD}$	Diode forward voltage	I <sub>SD</sub> = 25 A, V <sub>GS</sub> = 0 V	0.8	1	V
Q <sub>rr</sub>	Reverse recovery charge	V <sub>DS</sub> = 30 V, I <sub>F</sub> = 25 A,	139		nC
t <sub>rr</sub>	Reverse recovery time	di/dt = 300 A/μs	64		ns

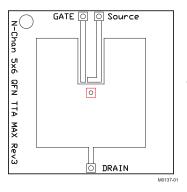
# 5.2 Thermal Information

T<sub>A</sub> = 25°C unless otherwise stated

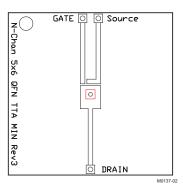
	THERMAL METRIC	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-case thermal resistance <sup>(1)</sup>			0.8	°C/W
$R_{\theta JA}$	Junction-to-ambient thermal resistance <sup>(1)(2)</sup>			50	°C/W

 <sup>(1)</sup> R<sub>θJC</sub> is determined with the device mounted on a 1-in² (6.45-cm²), 2-oz (0.071-mm) thick Cu pad on a 1.5-in x 1.5-in (3.81-cm x 3.81-cm), 0.06-in (1.52-mm) thick FR4 PCB. R<sub>θJC</sub> is specified by design, whereas R<sub>θJA</sub> is determined by the user's board design.
 (2) Device mounted on FR4 material with 1-in² (6.45-cm²), 2-oz (0.071-mm) thick Cu.





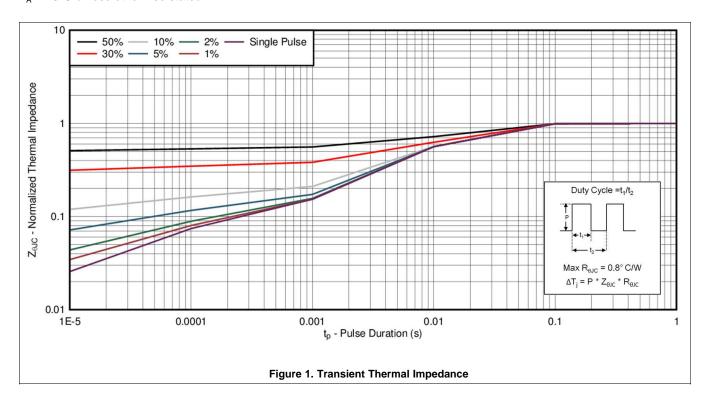
Max  $R_{\theta JA} = 50^{\circ}\text{C/W}$  when mounted on 1 in<sup>2</sup> (6.45 cm<sup>2</sup>) of 2-oz (0.071-mm) thick Cu.



Max  $R_{\theta JA} = 125^{\circ} C/W$  when mounted on a minimum pad area of 2-oz. (0.071-mm) thick Cu.

# 5.3 Typical MOSFET Characteristics

 $T_A = 25$ °C unless otherwise stated



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# **Typical MOSFET Characteristics (continued)**

T<sub>A</sub> = 25°C unless otherwise stated

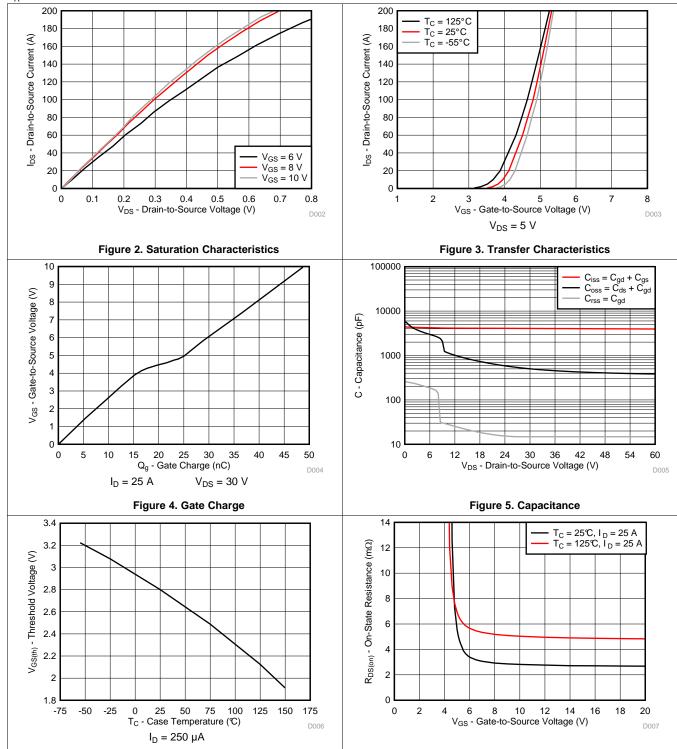


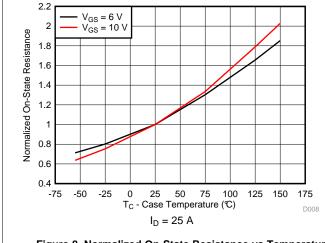
Figure 6. Threshold Voltage vs Temperature

Figure 7. On-State Resistance vs Gate-to-Source Voltage

# TEXAS INSTRUMENTS

# **Typical MOSFET Characteristics (continued)**

 $T_A = 25$ °C unless otherwise stated



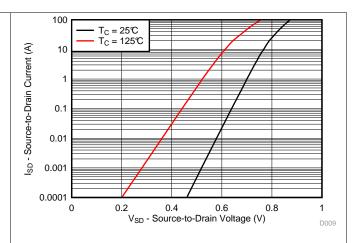
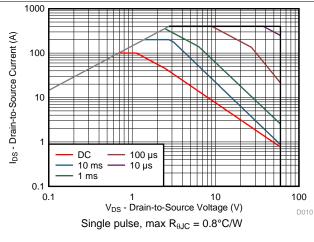


Figure 8. Normalized On-State Resistance vs Temperature





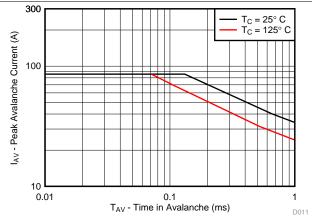


Figure 10. Maximum Safe Operating Area

Figure 11. Single Pulse Unclamped Inductive Switching

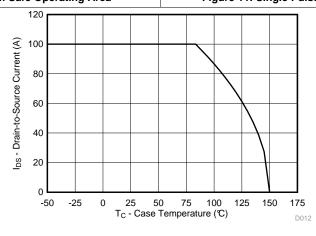


Figure 12. Maximum Drain Current vs Temperature

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# 6 Device and Documentation Support

### 6.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 6.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

#### 6.3 Trademarks

NexFET, E2E are trademarks of Texas Instruments.

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#### 6.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### 6.5 Glossary

SLYZ022 — TI Glossary.

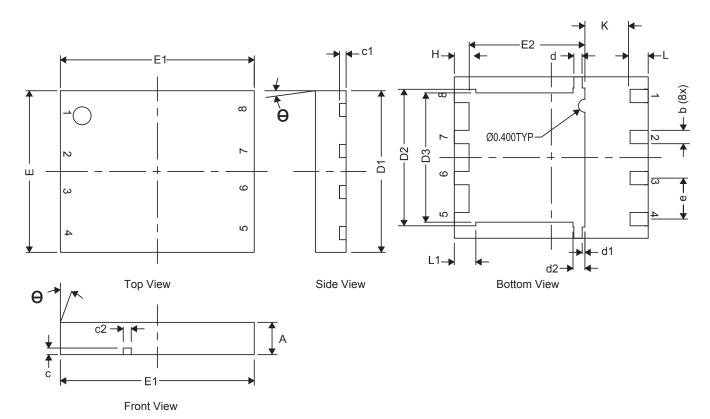
This glossary lists and explains terms, acronyms, and definitions.



# 7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

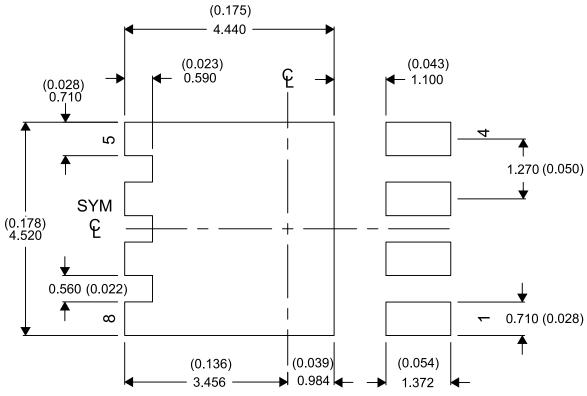
## 7.1 Q5B Package Dimensions



DIM	MILLIMETERS								
DIM	MIN	NOM	MAX						
Α	0.80	1.00	1.05						
b	0.36	0.41	0.46						
С	0.15	0.20	0.25						
c1	0.15	0.20	0.25						
c2	0.20	0.25	0.30						
D1	4.90	5.00	5.10						
D2	4.12	4.22	4.32						
d	0.20	0.25	0.30						
Е	4.90	5.00	5.10						
E1	5.90	6.00	6.10						
E2	3.48	3.58	3.68						
е		1.27 TYP							
L	0.46	0.56	0.66						
θ	0°	_							
K		1.40 TYP							

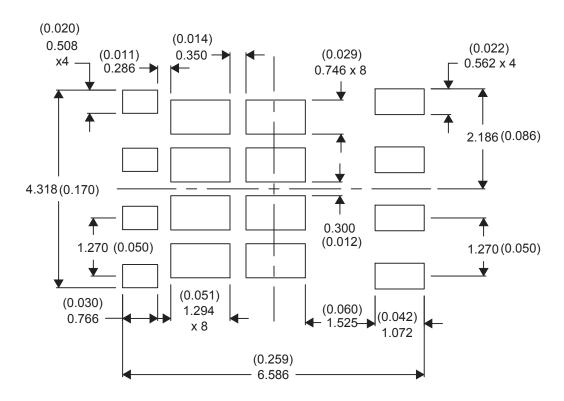


### 7.2 Recommended PCB Pattern



For recommended circuit layout for PCB designs, see *Reducing Ringing Through PCB Layout Techniques* (SLPA005).

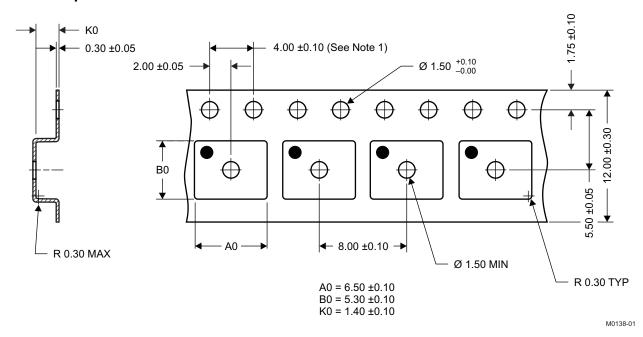
## 7.3 Recommended Stencil Pattern



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## 7.4 Q5B Tape and Reel Information



### Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2.
- 2. Camber not to exceed 1 mm in 100 mm, noncumulative over 250 mm.
- 3. Material: black static-dissipative polystyrene.
- 4. All dimensions are in mm (unless otherwise specified).
- 5. A0 and B0 measured on a plane 0.3 mm above the bottom of the pocket.



# PACKAGE OPTION ADDENDUM

20-Feb-2018

#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
CSD18532NQ5B	ACTIVE	VSON-CLIP	DNK	8	2500	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM	-55 to 150	18532N	Samples
CSD18532NQ5BT	ACTIVE	VSON-CLIP	DNK	8	250	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM	-55 to 150	18532N	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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# PACKAGE MATERIALS INFORMATION

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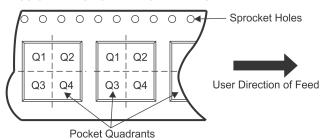
# TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD18532NQ5B	VSON- CLIP	DNK	8	2500	330.0	12.4	6.3	5.3	1.2	8.0	12.0	Q1
CSD18532NQ5B	VSON- CLIP	DNK	8	2500	330.0	12.8	6.5	5.3	1.4	8.0	12.0	Q1
CSD18532NQ5BT	VSON- CLIP	DNK	8	250	330.0	12.8	6.5	5.3	1.4	8.0	12.0	Q1
CSD18532NQ5BT	VSON- CLIP	DNK	8	250	330.0	12.4	6.3	5.3	1.2	8.0	12.0	Q1

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\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD18532NQ5B	VSON-CLIP	DNK	8	2500	335.0	335.0	32.0
CSD18532NQ5B	VSON-CLIP	DNK	8	2500	335.0	335.0	32.0
CSD18532NQ5BT	VSON-CLIP	DNK	8	250	335.0	335.0	32.0
CSD18532NQ5BT	VSON-CLIP	DNK	8	250	335.0	335.0	32.0

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